

Electronic Supplementary Information

Co-sputtered phase-change Ga-Sb-Te thin films

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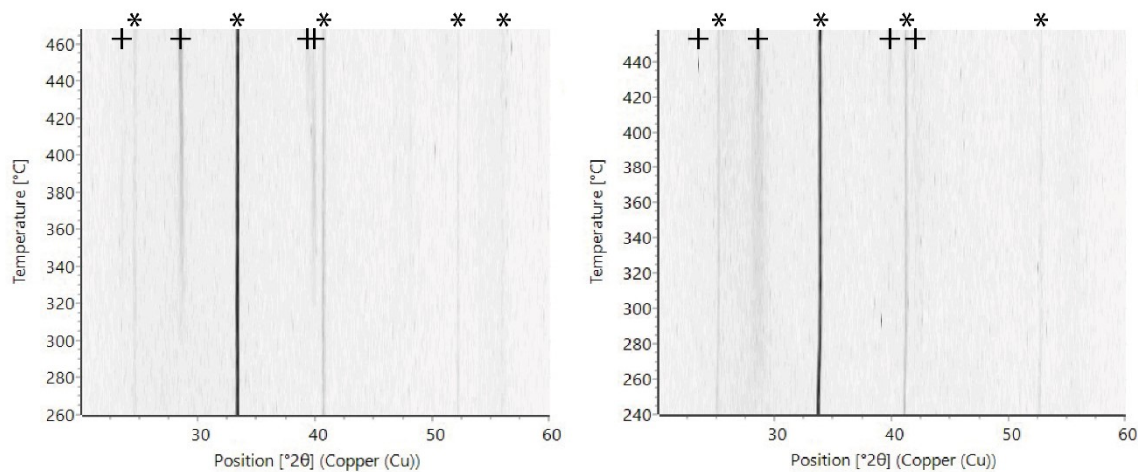


Figure S1 Temperature-dependent XRD plots of $\text{Ga}_5\text{Sb}_3\text{Te}_2$ (left) and $\text{Ga}_3\text{Sb}_3\text{Te}_2$ (right) thin films (100 nm). '*' symbol denotes the peaks originating from the substrate, '+' symbol denotes the peaks originating from the layer.

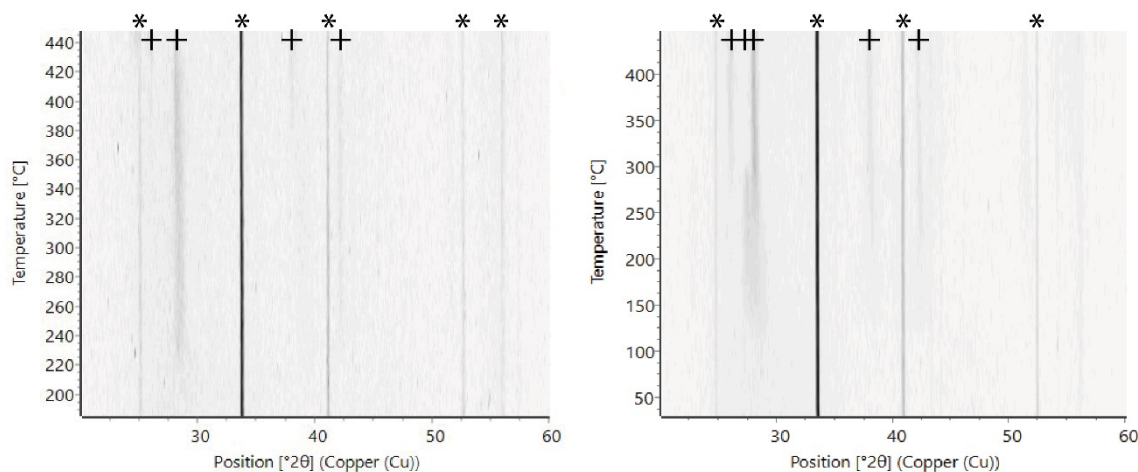


Figure S2 Temperature-dependent XRD plots of $\text{Ga}_2\text{Sb}_2\text{Te}_3$ (left) and GaSbTe_4 (right) thin films (100 nm). '*' symbol denotes the peaks originating from the substrate, '+' symbol denotes the peaks originating from the layer.

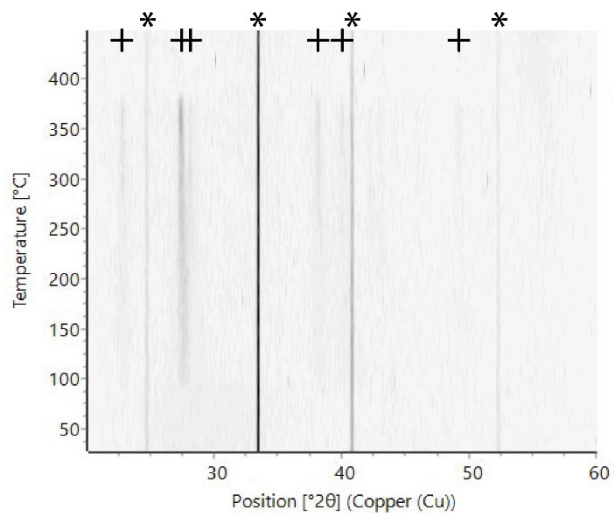


Figure S3 Temperature-dependent XRD plots of GaSbTe_3 thin film (100 nm). '*' symbol denotes the peaks originating from the substrate, '+' symbol denotes the peaks originating from the layer.